

Session 27

27. Oxide TFT IV

Thursday, October 13, 2011 / 09:00 ~ 10:30

Room 303

Chairs: Yeon Gon Mo (Samsung Mobile Display Co., Ltd., Korea)
Chi-Sun Hwang (ETRI, Korea)

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- 09:00 ~ 09:25** **27-1** **[Invited] Low Temperature Produced Metal Oxide Semiconductors and Dielectrics for Thin Film Transistors**
William Milne, F. M. Li, M. Mann, R. Waddingham, A. Kiani, S. M-L. Pfaendler, and A. J. Flewitt (Univ. of Cambridge, UK)
- 09:25 ~ 09:50** **27-2** **[Invited] High Performance of Buried Oxide Thin Film Transistor**
Sang Yeol Lee (KIST, Korea)
- 09:50 ~ 10:10** **27-3** **Effect of Indium content on amorphous Indium Tin Zinc Oxide Thin-Film Transistors**
Se Hee Park, Dae-Hwan Kim, Sul Lee, Hoon Yim, Jong-Uk Bae, Chang-Dong Kim, Myungchul Jun, and Yong Kee Hwang (LG Display Co., Ltd., Korea)
- 10:10 ~ 10:30** **27-4** **The Role of the Adsorbed Water on the Transfer Characteristics of Soluble Processed Zinc Tin Oxide Thin Film Transistors**
Doohyun Kim, Soobok Yoon (Korea Univ., Korea), YeonTaek Jeong, YoungMin Kim, BoSung Kim (Samsung Electronics Co., Ltd., Korea), and MunPyo Hong (Korea Univ., Korea)